

Description

The AOD417-HXY uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

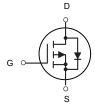


TO-252

General Features

 $V_{DS} = -30V I_{D} = -40A$

 $R_{DS(ON)}$ < 23 m Ω @ V_{GS} =10V



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AOD417-HXY	TO252-2L	40P03 XXX YYYY	2500

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	Drain-Source Voltage -30			
VGS	Gate-Source Voltage	Gate-Source Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ -40			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	-25	А		
IDM	Pulsed Drain Current ²	Pulsed Drain Current ² -70			
P _D @T _C =25°C	Total Power Dissipation ⁴	Total Power Dissipation ⁴ 34.7			
TSTG	Storage Temperature Range	Storage Temperature Range -55 to 150			
TJ	Operating Junction Temperature Range -55 to 150		°C		
ReJA	Thermal Resistance Junction-ambient ¹	tance Junction-ambient ¹ 62			
R _θ JC	Thermal Resistance Junction-Case ¹ 3.6		°C/W		



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.022		V/°C
Б	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-15A		18	23	m O
R _{DS(ON)}	Static Dialii-Source On-Resistance	V _{GS} =-4.5V , I _D =-10A		37	44	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} . In =-250uA	-1.0		-2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS=VDS, ID =-250UA		4.6		mV/°C
l	Drain Source Lookage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			-1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55°C			-5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-10A		5		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13		Ω
Q_g	Total Gate Charge (-4.5V)			12.5		
Q_{gs}	Gate-Source Charge	V_{DS} =-15V , V_{GS} =-4.5V , I_{D} =-15A		5.4		nC
Q_gd	Gate-Drain Charge			5		
$T_{d(on)}$	Turn-On Delay Time			4.4		
Tr	Rise Time	V_{DD} =-15V , V_{GS} =-10V , R_{G} =3.3 Ω ,		11.2		20
$T_{d(off)}$	Turn-Off Delay Time	I _D =-15A		34		ns
Tf	Fall Time			18		
Ciss	Input Capacitance			1345		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		194		pF
Crss	Reverse Transfer Capacitance			158		

Diode Characteristics

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Is	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			-40	Α
I _{SM}	Pulsed Source Current ^{2,5}	VG=VD=OV, Force Current			-75	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V
t _{rr}	Reverse Recovery Time	IF=-15A , dI/dt=100A/μs ,		12.4		nS
Q_{rr}	Reverse Recovery Charge	TJ=25°C		5		nC

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-38A
- 4.The power dissipation is limited by 150 $^{\circ}\text{C}\;$ junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

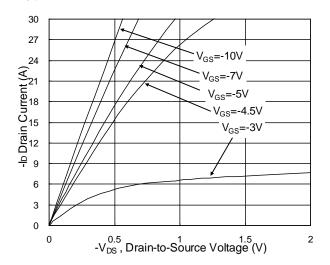


Fig.1 Typical Output Characteristics

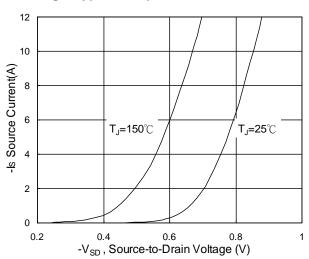


Fig.3 Forward Characteristics of Reverse

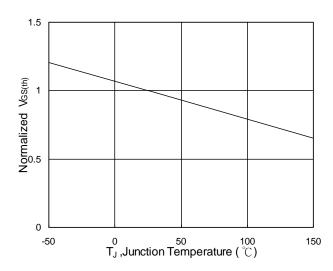


Fig.5 Normalized V_{GS(th)} v.s T_J

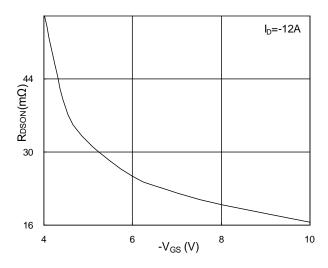


Fig.2 On-Resistance v.s Gate-Source

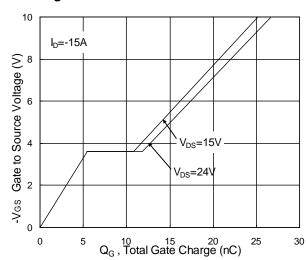


Fig.4 Gate-Charge Characteristics

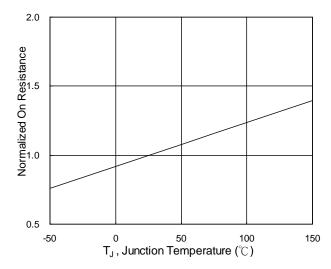
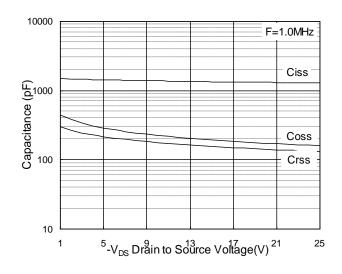


Fig.6 Normalized R_{DSON} v.s T_J





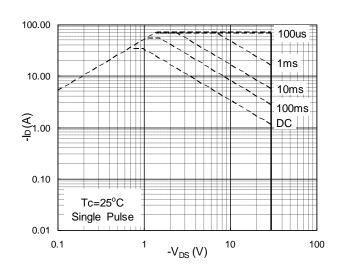


Fig.7 Capacitance

Fig.8 Safe Operating Area

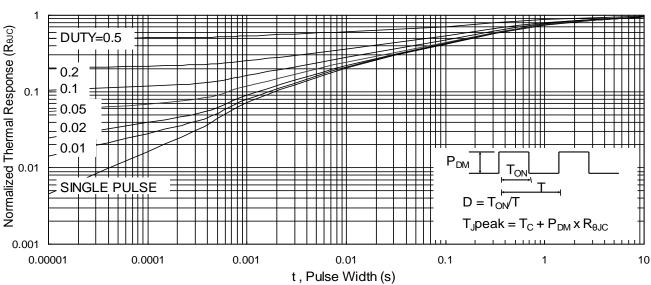


Fig.9 Normalized Maximum Transient Thermal Impedance

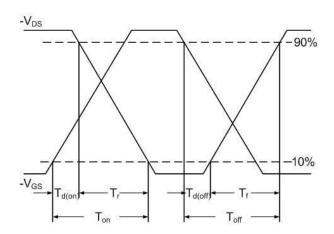


Fig.10 Switching Time Waveform

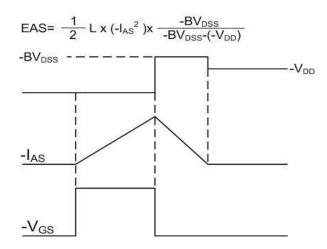
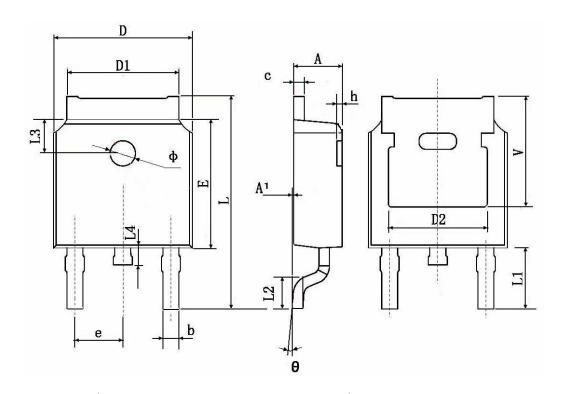


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	0.483	0.483 TYP.		0 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600	1.600 TYP.		3 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	5.350 TYP. 0.211 TYP.				

P-Channel Enhancement Mode MOSFET

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